

L Number	Hits	Search Text	DB	Time stamp
229	283	pixel near electrode near5 (substrate) near5 ito	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2004/07/08 10:27
230	7	("5162933" "5608557" "5760854" "5815223" "5818550" "5897182" "5939788").PN.		2004/07/08 09:54
231	1	6111619.URPN.	USPAT	2004/07/08 09:58
232	7	("4997785" "5130829" "5272370" "5407866" "5968850" "6100951" "6221792").PN.	USPAT	2004/07/08 10:09
233	489	pixel near electrode near4 (directly or on or upon or over) near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 10:28
234	382	pixel near electrode near3 (directly or on or upon or over) near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 10:28
236	208	pixel near electrode near3 (directly or on or upon or over) near substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 10:29
237	6	("4266223" "4602192" "5294869" "5294870" "5384517" "5550066").PN.	USPAT	2004/07/08 10:52
238	8	5897328.URPN.	USPAT	2004/07/08 10:52
239	9	(US-6580226-\$ or US-6559477-\$ or US-6346978-\$ or US-6275061-\$ or US-6087730-\$ or US-5938942-\$ or US-5815223-\$ or US-6252247-\$).did. or (US-20020053668-\$).did.	USPAT; USPAT; US-PGPUB	2004/07/08 11:51
240	35	flat near panel and planarization near5 (masking or photoresist or photolithography)	USPAT; US-PGPUB	2004/07/08 11:53
241	56	flat near panel and planarization near5 (photoresist or resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:56
242	172	(tft or thin near film near transistor) and (planarization or planar or planarized or planarize or planarizing) near5 (photoresist or resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 12:08
243	2	5010027.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 12:11
244	5230	(display) and (tft or thin adj film adj electrode) and (pixel adj electrode or anode near electrode or ito) near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 12:13
245	6312	(display) and (tft or thin adj film adj electrode) and (ito or transparent adj electrode or pixel adj electrode) near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 12:13
246	4	(display) and (tft or thin adj film adj electrode) and (gate adj oxide or gate adj insulating or gate adj insulator) near2 (upon or on or top or over or above) near2 (ito or transparent adj electrode or pixel adj electrode) near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 12:15

247	22	(display) and (tft or thin adj film adj electrode) and (gate adj oxide or gate adj insulating or gate adj insulator) near2 (upon or on or top or over or above) near2 (ito or transparent adj electrode or pixel adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 12:18
248	86	(display) and (tft or thin adj film adj electrode) and (gate adj oxide or gate adj insulating or gate adj insulator) near5 (upon or on or top or over or above) near5 (ito or transparent adj electrode or pixel adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 12:18
-	17045	(tft or thin near film near transistor or amorphous near2 silicon or polycrystalline near2 silicon or poly near2 silicon or polysilicon or poly near2 si) and pixel near electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/06 15:55
-	1593	(tft or thin near film near transistor or amorphous near2 silicon or polycrystalline near2 silicon or poly near2 silicon or polysilicon or poly near2 si) and pixel near electrode and (flat near panel near2 display)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/06 15:56
-	1562	(tft or thin near film near transistor) and pixel near electrode and (flat near panel near2 display)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/06 15:56
-	834	(tft or thin near film near transistor or amorphous near2 silicon or polycrystalline near2 silicon or poly near2 silicon or polysilicon or poly near2 si) and (pixel near electrode) near8 (substrate) and (flat near panel near2 display)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/06 15:57
-	696	(tft or thin near film near transistor or amorphous near2 silicon or polycrystalline near2 silicon or poly near2 silicon or polysilicon or poly near2 si) and (pixel near electrode) near5 (substrate) and (flat near panel near2 display)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/06 15:57
-	428	(tft or thin near film near transistor or amorphous near2 silicon or polycrystalline near2 silicon or poly near2 silicon or polysilicon or poly near2 si) and (pixel near electrode) near8 (substrate) and (flat near panel near2 display) and (source or drain or channel or polycrystalline near silicon or polysilicon or polycrystalline near si or amorphous near silicon or a-si) near8 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/07 16:05
-	8	("4963701" "5083190" "5130829" "5272370" "5298312" "5407866" "5691090" "5691782").PN.	USPAT	2004/07/07 15:50
-	141	top near gate near2 (tft or thin near film near transistor) and (flat near2 panel) and pixel near electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 09:37
-	8	6087730.URPN.	USPAT	2004/07/07 16:16
-	2	5130829.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/07 16:22